

Date:- 13th Oct 2011

Data Sheet Issue:- 2

Provisional Data

Rectifier Diode

Types W104CF#200 to W104CF#220

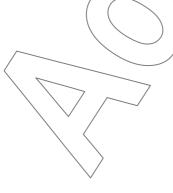
Absolute Maximum Ratings

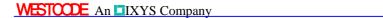
	VOLTAGE RATINGS		MAXIMUM LIMITS	UNITS
V_{RRM}	Repetitive peak reverse voltage, (note 1)		2000-2200	V
V_{RSM}	Non-repetitive peak reverse voltage, (note 1)		2100-2300	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
I _{F(AV)M}	Maximum average forward current, T _{sink} =55°C, (note 2)	10450	А
$I_{F(AV)M}$	Maximum average forward current. T _{sink} =100°C, (note 2)	7725	Α
$I_{F(AV)M}$	Maximum average forward current. T _{sink} =100°C, (note 3)	4815	Α
I _{F(RMS)}	Nominal RMS forward current, T _{sink} =25°C _x (note 2)	18825	Α
I _{F(d.c.)}	D.C. forward current, T _{sink} =25°C, (note 4)	16600	Α
I _{FSM}	Peak non-repetitive surge t _p =10ms/V _m =60%V _{RRM} , (note 5)	83.7	kA
I _{FSM2}	Peak non-repetitive surge t _p =10ms, V _m ≤10V, (note 5)	92.0	kA
l ² t	I^2 t capacity for fusing t_p =10ms, V_{rm} =60% V_{RRM} , (note 5)	35.0×10 ⁶	A ² s
l ² t	I ² t capacity for fusing t _p =10ms, V _{rm} ≤10V, (note 5)	42.3×10 ⁶	A ² s
T _{j op}	Operating temperature range	-40 to +175	°C
T _{stg}	Storage temperature range	-55 to +175	°C

Notes:

- 1) De-rating factor of 0.13% per °C is applicable for T_j below 25°C.
- 2) Double side cooled, single phase, 50Hz, 180° half-sinewave.
- 3) Single side cooled, single phase; 50Hz, 180° half-sinewave.
- 4) Double side cooled
- 5) Half-sinewave, 175°C T_k initial.





Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V_{FM}	Maximum peak forward voltage	-	-	0.9	I _{FM} =4500A	V
V_{FM}	Maximum peak forward voltage	-	-	1.04	I _{FM} =8000A	V
V_{T0}	Threshold voltage	-	-	0.709		V
r _T	Slope resistance	-	-	0.041		mΩ
	Peak reverse current	-	-	20	Rated V _{RRM} , T _/ =25°C	mA
I _{RRM}	reak reverse current	-	-	200	Rated V _{RRM}	IIIA
Q_{rr}	Recovered charge	-	6600	7500		μC
Q_{ra}	Recovered charge, 50% Chord	-	5800	- /	I _{TM} =4000A, t _p =2000μs, di/dt=10A/μs,	μC
I _{rm}	Reverse recovery current	-	280	<- <	V _r =100V	Α
t _{rr}	Reverse recovery time, 50% chord	-	41	-		μs
_	The armost an electrical contains to be established	-	-	0.0065	Double side cooled	K/W
R_{thJK}	Thermal resistance, junction to heatsink	-	-	0.0130	Single side cooled	K/W
F	Mounting force	81	- /	99	Note 2	kN
١٨/	Waight	-	2.0	\bigcirc /	ં ભૂtline option FD	ka
W _t	Weight	-	2.8	V-/	Out)ine options FC	kg

Notes:-

- 1) Unless otherwise indicated $T_j=175^{\circ}C$.
- 2) For other clamp forces, please consult factory.



Notes on Ratings and Characteristics

1.0 Voltage Grade Table

Voltage Grade	$egin{array}{c} V_{RRM} \ V \end{array}$	V _{RSM} V	V _R DC V
20	2000	2100	7 1250
22	2200	2300	1350

2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales/Production.

3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for Tibelow 25°C.

4.0 Snubber Components

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

5.0 Computer Modelling Parameters

5.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_{T0} + \sqrt{V_{T0}^{2} + 4 \cdot ff^{2} \cdot r_{T} \cdot W_{AV}}}{2 \cdot ff^{2} \cdot r_{T}}$$

$$W_{AV} = \frac{\Delta T}{R_{th}}$$
 $\Delta T = T_{j \max} - T_{K}$

Where V_{T0} =0.709V, r_T =0.041m Ω

 $R_{\it th}$ = Supplementary thermal impedance, see table below and

ff = Form factor, see table below.

Supplementary Thermal Impedance					
Conduction Angle	6 phase (60°)	3 phase (120°)	½ wave (180°)	d.c.	
Square wave Double Side Cooled	0.00707	0.00689	0.00673	0.0065	
Square wave Single Side Cooled	0.01359	0.01349	0.01323	0.0130	
Sine wave Double Side Cooled	0.00697	0.00678	0.00654		
Sine wave Single Side Cooled	0.01348	0.01328	0.01303		

Form Factors					
Conduc	ction Angle	6 phase (60°)	3 phase (120°)	½ wave (180°)	d.c.
Squa	are wave	2.449	1.732	1.414	1
Sine	e wave	2.778	1.879	1.57	

5.2 Calculating V_F using ABCD Coefficients

The on-state characteristic I_F vs. V_F, on page 6 is represented in two ways;

- the well established V_{T0} and r_T tangent used for rating purposes and
- (ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for terms of I_F given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for V_F agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		175°C Coefficients		
Α	0.7528241	Α	0.3017991	
В	8.33323×10 ⁻³	В	0.04496923	
С	3.26735×10 ⁻⁶	(ç_	2,19531×10⁻⁵	
D	3.115014×10 ⁻³		1.759866×10 ⁻³	

5.3 D.C. Thermal Impedance Calculation

$$r_{t} = \sum_{p=1}^{p=n} r_{p} \cdot \left(1 - e^{\frac{-t}{\tau_{p}}}\right)$$

Where p = 1 to n, n is the number of terms in the series and:

- t = Duration of heating pulse in seconds.
- r, = Thermal resistance at time t.
- r_p = Amplitude of p_{th} term. r_p = Time Constant of r_{th} term.

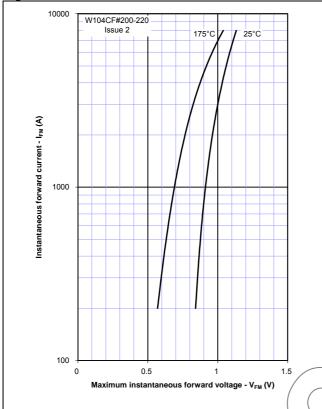
The coefficients for this device are shown in the tables below:

	D.C. Double Side Cooled						
Term	4	2	3	4			
r_p	3.424745×10 ⁻³	1.745273×10 ⁻³	8.532017×10 ⁻⁴	3.457329×10 ⁻⁴			
$ au_{\mathcal{p}}$	1.125391	0.1878348	0.02788979	8.430889×10 ⁻³			

D.C. Single Side Cooled						
Term	2	3	4			
8.375269×10 ⁻³	2.518437×10 ⁻³	1.193758×10 ⁻³	7.45432×10 ⁻⁴			
τ_{p} 8.929845	0.4711304	0.08221244	0.01221961			

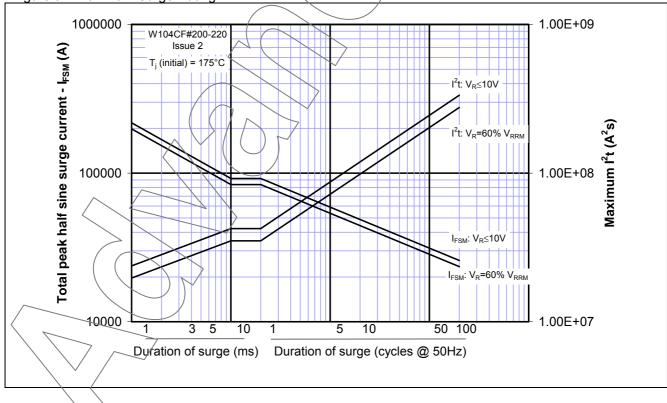
Curves

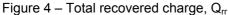




0.1 W104CF#200-220 Issue 2 0.001 0.001 0.01 0.1 1 10 100 Time (s)

Figure 3 – Maximum Surge Rating





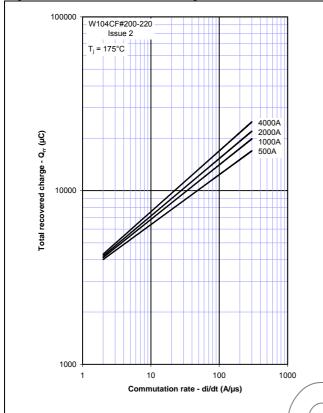
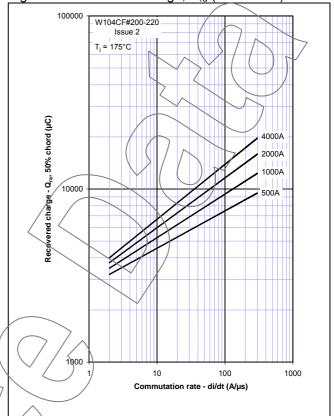


Figure 5 – Recovered charge, Q_{ra} (50% chord)



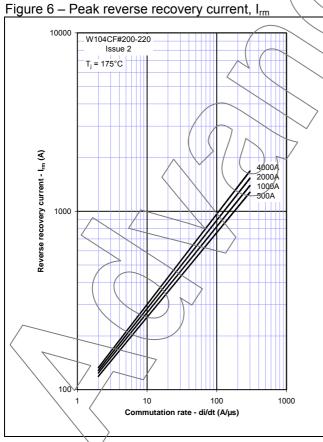


Figure 7 – Maximum recovery time, t_{rr} (50% chord)

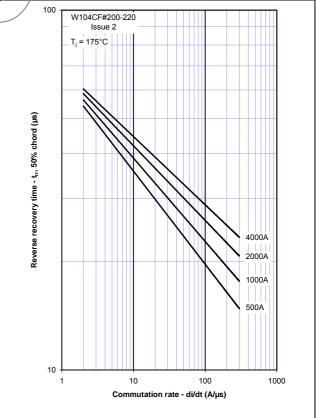


Figure 8 – Forward current vs. Power dissipation – Double Side Cooled

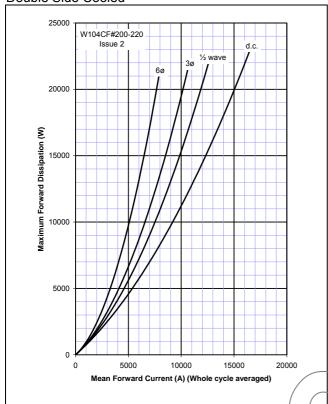


Figure 10 – Forward current vs. Power dissipation – Cathode Side Cooled

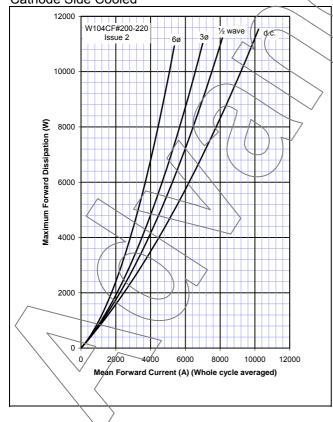


Figure 9 – Forward current vs. Heatsink temperature

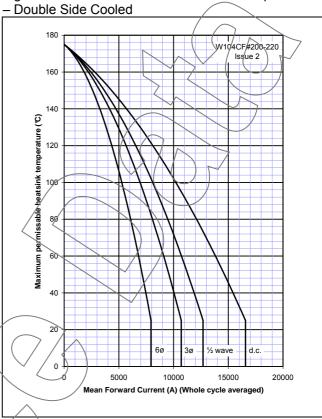
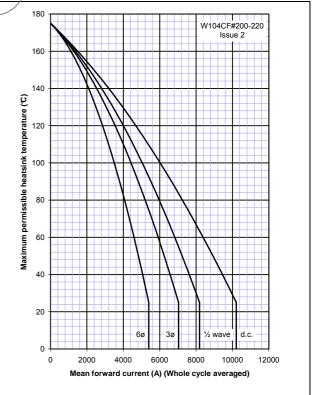
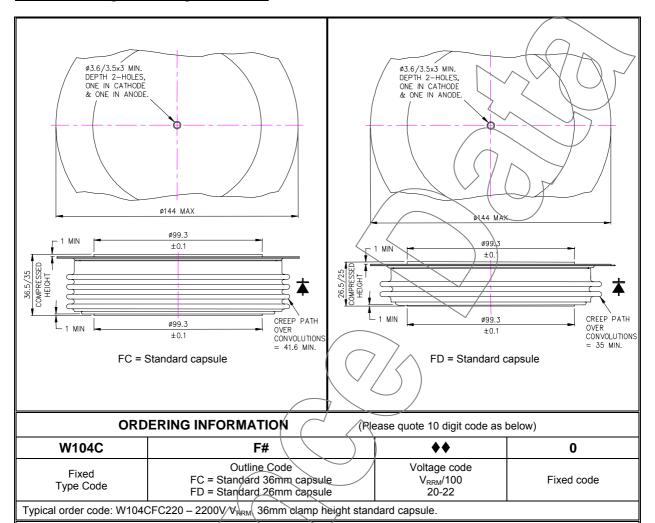


Figure 11 – Forward current vs. Heatsink temperature — Cathode Side Cooled



Outline Drawing & Ordering Information



IXYS Semiconductor GmbH

Edisonstraße 15 D-68623 Lampertheim

IXYS Corporation 1590 Buckeye Drive Milpitas CA 95035-7418 Tel: +1 (408) 457 9000

Fax: +1 (408) 496 0670 E-mail: sales@ixys.net AN ULXYS Company

www.westcode.com

www.ixys.net

Westcode Semiconductors Ltd

Langley Park Way, Langley Park, Chippenham. Wiltshire. SN15 1GE.

IXYS Long Beach

IXYS Long Beach, Inc 2500 Mira Mar Ave, Long Beach CA 90815

Tel: +1 (562) 296 6584 Fax: +1 (562) 296 6585

E-mail: service@ixyslongbeach.com

The information contained herein is confidential and is protected by Copyright. The information may not be used or disclosed except with the written permission of and in the manner permitted by the proprietors Westcode Semiconductors Ltd.

In the interest of product improvement, Westcode reserves the right to change specifications at any time without prior notice.

Devices with a suffix code (2-letter, 3-letter or letter/digit/letter combination) added to their generic code are not necessarily subject to the conditions and limits contained in this report.

© Westcode Semiconductors Ltd.